

## CLAIMS:

1. A discrete semiconductor component, and in particular a magnetoresistive sensor, having
  - an active circuit that is provided in an active layer (10) on the surface of a substrate,
  - 5 - at least one bond pad (12, 14, 16, 18) that in each case forms a bonding surface for a bond wire (22, 24, 26, 28), and
  - electrical connections (20) between the at least one bond pad and the active circuit,characterized in that the bond pad or pads (12, 14, 16, 18) is or are arranged above the active  
10 layer (10).
2. A discrete semiconductor component as claimed in claim 1, characterized in that the bond pad or pads (12, 14, 16, 18) cover the active layer (10) substantially completely.
- 15 3. A discrete semiconductor component as claimed in claim 1, characterized in that the electrical connections pass through a passivating layer to the active layer (10).
4. A discrete semiconductor component as claimed in claim 3, characterized in that the passivating layer contains silicon oxide or silicon nitride.  
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5. A discrete semiconductor component as claimed in one of claims 1 to 4, characterized in that the bond pads (12, 14, 16, 18) are composed of aluminum or an aluminum alloy.
- 25 6. A discrete semiconductor component as claimed in one of claims 1 to 5, characterized in that the bond wire (22, 24, 26, 28) is composed of gold or a gold alloy.
7. A method of producing a discrete semiconductor component, having the steps of

- providing a substrate having an active layer that has an active circuit,
- applying a passivating layer to the active layer,

characterized by

- the arrangement of one or more bond pads on the passivating layer and
- 5 - the through-passage of electrical connections from the bond pad or pads to the active circuit.